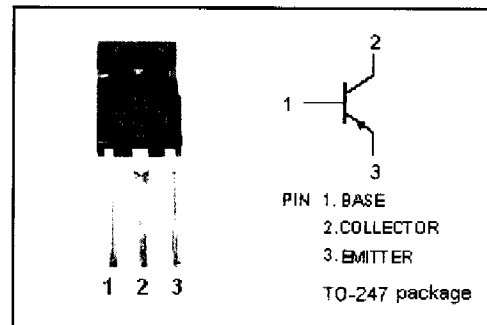


**Silicon PNP Power Transistor**

**2SB1477**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
 :  $V_{(BR)CEO} = -100V(\text{Min.})$
- Wide Area of Safe Operation
- Complement to Type 2SD2236

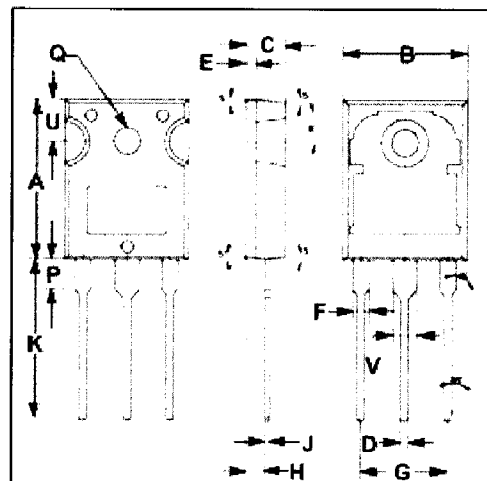


**APPLICATIONS**

- Designed for driver and general purpose applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-100	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_c$	Collector Current-Continuous	-5	A
$P_c$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	60	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55-150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



## Silicon PNP Power Transistor

## 2SB1477

### ELECTRICAL CHARACTERISTICS

$T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Beakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	100			V
$V_{(BR)CBO}$	Collector-Base Beakdown Voltage	$I_C = -50\ \mu\text{A}; I_E = 0$	100			V
$V_{(BR)EBO}$	Emitter-Base Beakdown Voltage	$I_E = -50\ \mu\text{A}; I_C = 0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-2.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -100\text{V}; I_E = 0$			-10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	60		320	

#### ◆ $h_{FE}$ Classifications

D	E	F
60-120	100-200	160-320